NSN 5962-01-367-1280

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View Online at https://aerobasegroup.com/nsn/5962-01-367-1280

Body	Length:
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Between 1.270 inches and 1.290 inches

Body Width:

Between 0.300 inches and 0.320 inches

Body Height:

Between 0.190 inches and 0.210 inches

Maximum Power Dissipation Rating:

650.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Eo lorops

Features Provided:

Erasable and programmed and ultraviolet erasable and electrostatic sensitive

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Criticality Code Justification:

Feat

Case Outline Source And Designator:

D-9 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed

Voltage Rating And Type Per Characteristic:

-2.0 volts total supply and 7.0 volts total supply

Time Rating Per Chacteristic:

55.00 nanoseconds af output megawatts

Memory Device Type:

Pal

Special Features:

Esd; altered item programmed using 67268/5962-8686401lx using file 1055_u56.Jed with check sum 37de

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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T	erm	inal	Type	Δnd	Ou	antity	,.
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24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0